

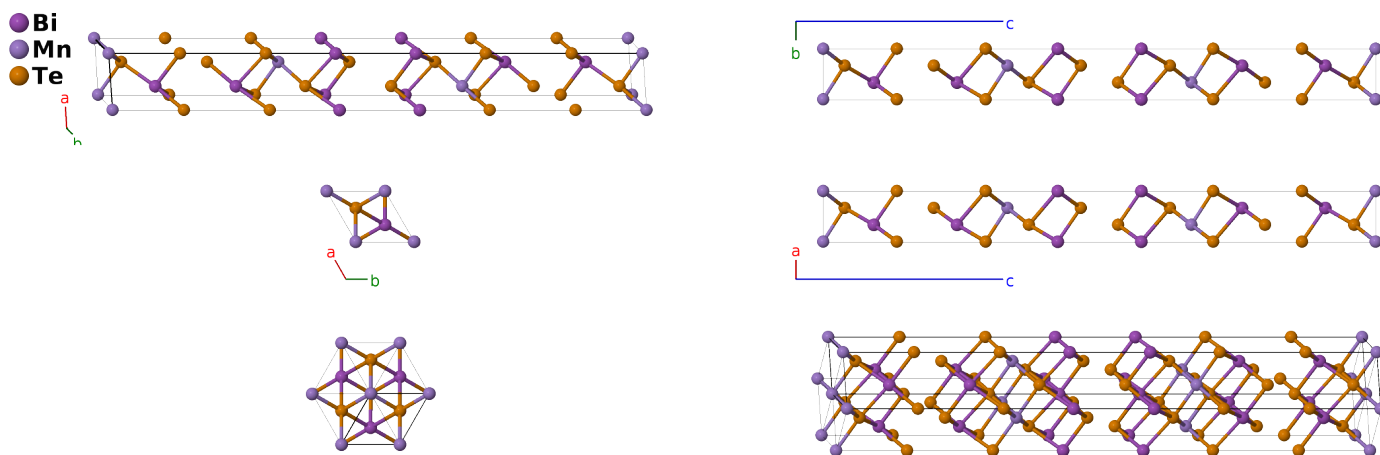
MnBi₂Te₄ Structure: A2BC4_hR7_166_c_a_2c-002

This structure originally had the label A2BC4_hR7_166_c_a_2c. Calls to that address will be redirected here.

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<https://aflow.org/p/MU2V>

https://aflow.org/p/A2BC4_hR7_166_c_a_2c-002



Prototype	Bi ₂ MnTe ₄
AFLOW prototype label	A2BC4_hR7_166_c_a_2c-002
ICSD	37566
Pearson symbol	hR7
Space group number	166
Space group symbol	$R\bar{3}m$
AFLOW prototype command	<code>aflow --proto=A2BC4_hR7_166_c_a_2c-002 --params=a, c/a, x₂, x₃, x₄</code>

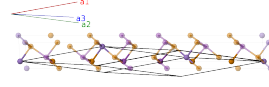
Other compounds with this structure

GeAs₂Te₄, MnSb₂Te₄, SSe₂Bi₄, Bi₃Se₄, Se₃Bi₄

- We use the data taken at 10K. Except for the magnetic ordering there is no substantial change in the structure up to room temperature.
- The ICSD entry is from the room-temperature measurements of (Aliev, 2019).
- This structure is nearly identical to GeSb₂Te₄, but the ordering of the tellurium atoms is different in the two cases.

Rhombohedral primitive vectors

$$\begin{aligned}\mathbf{a}_1 &= \frac{1}{2}a \hat{\mathbf{x}} - \frac{\sqrt{3}}{6}a \hat{\mathbf{y}} + \frac{1}{3}c \hat{\mathbf{z}} \\ \mathbf{a}_2 &= \frac{1}{\sqrt{3}}a \hat{\mathbf{y}} + \frac{1}{3}c \hat{\mathbf{z}} \\ \mathbf{a}_3 &= -\frac{1}{2}a \hat{\mathbf{x}} - \frac{\sqrt{3}}{6}a \hat{\mathbf{y}} + \frac{1}{3}c \hat{\mathbf{z}}\end{aligned}$$



Basis vectors

	Lattice coordinates		Cartesian coordinates	Wyckoff position	Atom type
\mathbf{B}_1	=	0	=	0	(1a) Mn I
\mathbf{B}_2	=	$x_2 \mathbf{a}_1 + x_2 \mathbf{a}_2 + x_2 \mathbf{a}_3$	=	$cx_2 \hat{\mathbf{z}}$	(2c) Bi I
\mathbf{B}_3	=	$-x_2 \mathbf{a}_1 - x_2 \mathbf{a}_2 - x_2 \mathbf{a}_3$	=	$-cx_2 \hat{\mathbf{z}}$	(2c) Bi I
\mathbf{B}_4	=	$x_3 \mathbf{a}_1 + x_3 \mathbf{a}_2 + x_3 \mathbf{a}_3$	=	$cx_3 \hat{\mathbf{z}}$	(2c) Te I
\mathbf{B}_5	=	$-x_3 \mathbf{a}_1 - x_3 \mathbf{a}_2 - x_3 \mathbf{a}_3$	=	$-cx_3 \hat{\mathbf{z}}$	(2c) Te I
\mathbf{B}_6	=	$x_4 \mathbf{a}_1 + x_4 \mathbf{a}_2 + x_4 \mathbf{a}_3$	=	$cx_4 \hat{\mathbf{z}}$	(2c) Te II
\mathbf{B}_7	=	$-x_4 \mathbf{a}_1 - x_4 \mathbf{a}_2 - x_4 \mathbf{a}_3$	=	$-cx_4 \hat{\mathbf{z}}$	(2c) Te II

References

- [1] J.-Q. Yan, Q. Zhang, T. Heitmann, Z. Huang, K. Y. Chen, J.-G. Cheng, W. Wu, D. Vaknin, B. C. Sales, and R. J. McQueeney, *Crystal growth and magnetic structure of $MnBi_2Te_4$* , Phys. Rev. Mat. **3**, 064202 (2019), doi:10.1103/PhysRevMaterials.3.064202.
- [2] Z. S. Aliev, I. R. Amiraslanov, D. I. Nasonova, A. V. Shevelkov, N. A. Abdullayev, Z. A. Jahangirli, E. N. Orujlu, M. M. Otrokov, N. T. Mamedov, M. B. Babanly, and E. V. Chulkov, *Novel ternary layered manganese bismuth tellurides of the $MnTe-Bi_2Te_3$ system: Synthesis and crystal structure*, J. Alloys Compd. **789**, 443–450 (2019), doi:10.1016/j.jallcom.2019.03.030.